

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-8. Canceled.

9. (Previously Presented) A method of making multiple radiation-emitting and/or radiation-receiving semiconductor components each comprising a radiation-emitting and/or radiation-receiving semiconductor chip, a molded plastic body which is transmissive to an electromagnetic radiation to be emitted and/or received by the semiconductor component and by which the semiconductor chip is at least partially overmolded, and external electrical leads that are electrically connected to electrical contact areas of the semiconductor chip, wherein

the semiconductor chip of each component is attached to a metallic lead frame, a carrier substrate or a flexible lead frame comprising the external electrical leads,

the semiconductor chip of each component, including subregions of the lead frame, the carrier substrate or the flexible lead frame, is placed in a respective cavity of an injection mold, and an injection channel is led through each of the multiple semiconductor components,

silicone molding compound is injected into the respective cavities through the injection channel via an injection molding process or a transfer molding process, and

the silicone molding compound is cured in the respective cavities at least such that in each cavity, a shape-stable molded plastic part is formed.

10-30. Canceled.

31. (Previously Presented) The method as in claim 9, wherein the silicone molding compound has a curing time of 10 minutes or less.

32. (Previously Presented) The method as in claim 9, wherein the semiconductor chip is attached to a flexible lead frame formed by a carrier film.

33. (Previously Presented) The method as in claim 32, further comprising forming the carrier film, wherein forming the carrier film comprises forming a laminate comprising a plastic film and a metal film.

34. (Previously Presented) The method as in claim 33, wherein forming the carrier film further comprises stamping the metal film to define a cathode and an anode for the semiconductor chip.

35. (Previously Presented) The method as in claim 34, wherein forming the carrier film further comprises stamping openings into the plastic film.

36. (Previously Presented) The method as in claim 34, wherein forming the carrier film further comprises stamping openings in the plastic film, the openings being arranged over the cathode and the anode.

37. (Previously Presented) The method as in claim 36, wherein the semiconductor chip is bonded to the cathode through one of the openings.

38-40. Canceled.